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November 2013

FDB16AN08A0

N-Channel PowerTrench[®] MOSFET 75 V, 58 A, 16 m Ω

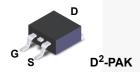
Features

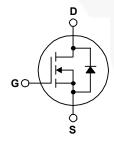
- $R_{DS(on)}$ = 13 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 58 A
- $Q_{G(tot)}$ = 28 nC (Typ.) @ V_{GS} = 10 V
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)

Formerly developmental type 82660

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FDB16AN08A0	Unit
$V_{\rm DSS}$	Drain to Source Voltage	75	V
V_{GS}	Gate to Source Voltage	±20	V
	Drain Current		/
	Continuous ($T_C = 25^{\circ}C$, $V_{GS} = 10V$)	58	Α
I_D	Continuous (T _C = 100°C, V _{GS} = 10V)	44	
	Continuous ($T_{amb} = 25^{\circ}C$, $V_{GS} = 10V$, with $R_{\theta JA} = 43^{\circ}C/W$)	9	Α
	Pulsed	Figure 4	Α
E _{AS}	Single Pulse Avalanche Energy (Note 1)	117	mJ
	Power dissipation	135	W
P_{D}	Derate above 25°C	0.9	W/°C
T _J , T _{STG}	Operating and Storage Temperature	-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case, Max.	1.11	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, Max.	62	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, 1in ² Copper Pad Area, Max.	43	°C/W

0.032

0.037

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB16AN08A0	FDB16AN08A0	D ² -PAK	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Chara	acteristics					
B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	75	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60V	-	1		
	Zero Gate voltage Drain Current	$V_{GS} = 0V$ $T_{C} = 150^{\circ}C$	-	-	250	μΑ
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20V	-	-	±100	nA
On Chara	acteristics					
V _{GS(TH)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2	-	4	V
		I _D = 58A, V _{GS} = 10V	-	0.013	0.016	
[DS(ON)	Drain to Source On Resistance	$I_D = 29A, V_{GS} = 6V$	-	0.019	0.029	Ω

 $I_D = 58A, V_{GS} = 10V,$ $T_J = 175^{\circ}C$

Dynamic Characteristics

r_{DS(ON)}

C _{ISS}	Input Capacitance	\/ - 25\/ \/	- 0)/	1	1857	ı	pF
C _{OSS}	Output Capacitance	$V_{DS} = 25V, V_{GS}$	$V_{DS} = 25V, V_{GS} = 0V,$		288	ı	pF
C _{RSS}	Reverse Transfer Capacitance	1 1111112		ı	88	ı	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V			28	42	nC
$Q_{g(TH)}$	Threshold Gate Charge	V_{GS} = 0V to 2V	V _{DD} = 40V	ı	3.5	5	nC
	Gate to Source Gate Charge		I _D = 58A	-	11	-	nC
Q _{gs} Q _{gs2}	Gate Charge Threshold to Plateau		$I_g = 1.0 \text{mA}$	-	7.6	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	6.4	-	nC

Switching Characteristics $(V_{GS} = 10V)$

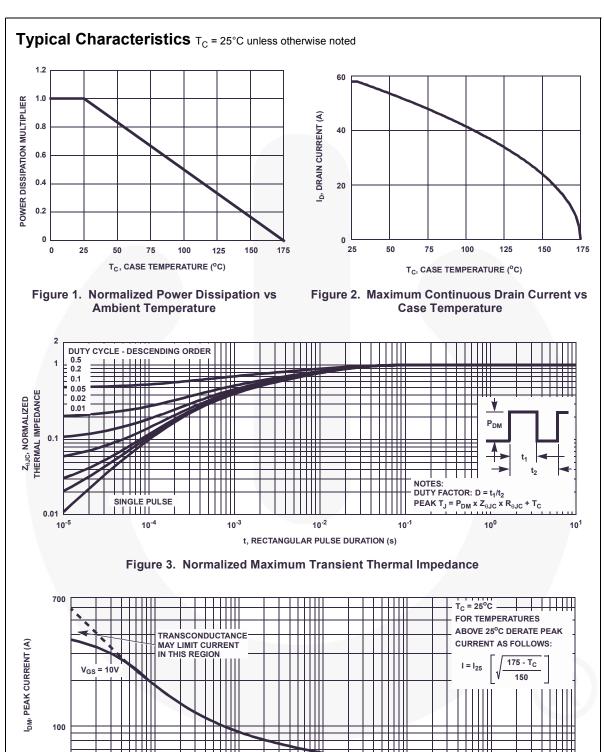
Drain to Source On Resistance

t _{ON}	Turn-On Time		-	-	135	ns
t _{d(ON)}	Turn-On Delay Time		/	8	-	ns
t _r	Rise Time	V _{DD} = 40V, I _D = 58A	-	82	-	ns
t _{d(OFF)}	Turn-Off Delay Time	$V_{GS} = 10V$, $R_{GS} = 10\Omega$	-	28	-	ns
t _f	Fall Time		-	30		ns
t _{OFF}	Turn-Off Time		-	-	86	ns

Drain-Source Diode Characteristics

V _{SD}	Source to Drain Diode Voltage	I _{SD} = 58A	-	-	1.25	V
	Source to Drain Diode Voltage	I _{SD} = 29A	-	1.0	1.0	V
t _{rr}	Reverse Recovery Time	$I_{SD} = 58A$, $dI_{SD}/dt = 100A/\mu s$	-	-	35	ns
Q _{RR}	Reverse Recovered Charge	$I_{SD} = 58A$, $dI_{SD}/dt = 100A/\mu s$	-	-	36	nC

Notes: 1: Starting $T_J = 25^{\circ}C$, $L = 260 \mu H$, $I_{AS} = 30 A$.



10⁻²

t, PULSE WIDTH (s)

10⁻³

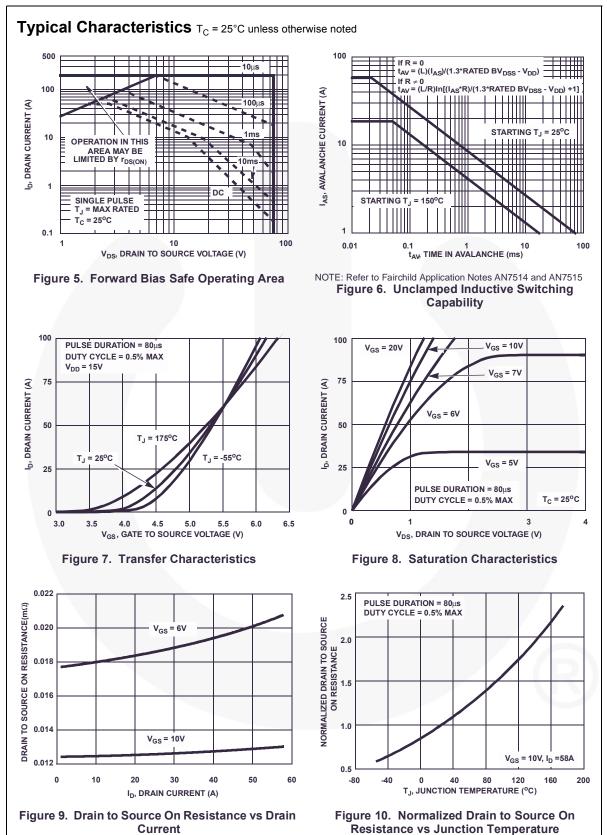
10⁻¹

10⁰

10⁻⁴

50 └ 10⁻⁵

10¹



Typical Characteristics T_C = 25°C unless otherwise noted

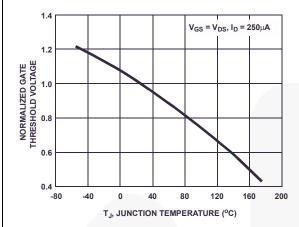


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

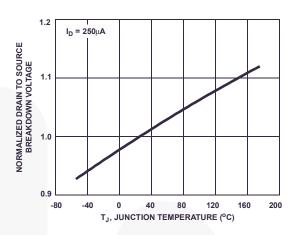


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

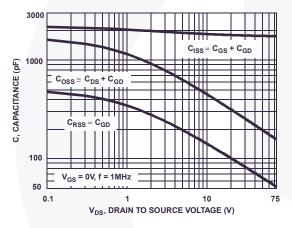


Figure 13. Capacitance vs Drain to Source Voltage

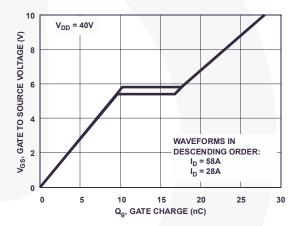


Figure 14. Gate Charge Waveforms for Constant Gate Current

Test Circuits and Waveforms

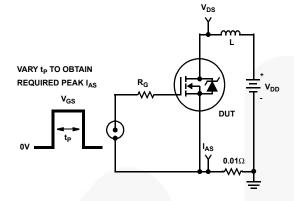


Figure 15. Unclamped Energy Test Circuit

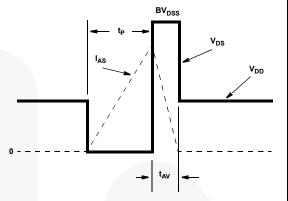


Figure 16. Unclamped Energy Waveforms

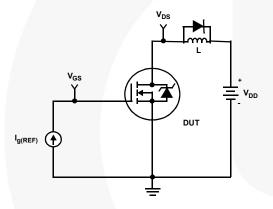


Figure 17. Gate Charge Test Circuit

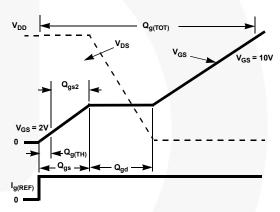


Figure 18. Gate Charge Waveforms

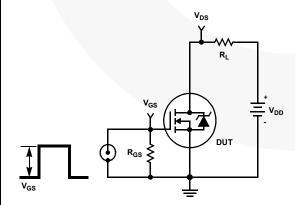


Figure 19. Switching Time Test Circuit

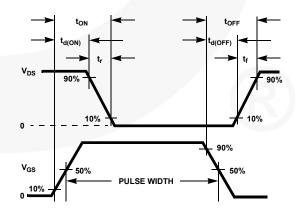


Figure 20. Switching Time Waveforms

Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature, T_{JM} , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, P_{DM} , in an application. Therefore the application's ambient temperature, T_A (°C), and thermal resistance $R_{\theta JA}$ (°C/W) must be reviewed to ensure that T_{JM} is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}} \tag{EQ. 1}$$

In using surface mount devices such as the TO-263 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of P_{DM} is complex and influenced by many factors:

- Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
- The number of copper layers and the thickness of the board.
- 3. The use of external heat sinks.
- 4. The use of thermal vias.
- 5. Air flow and board orientation.
- 6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 21 defines the $R_{\theta JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

Thermal resistances corresponding to other copper areas can be obtained from Figure 21 or by calculation using Equation 2 or 3. Equation 2 is used for copper area defined in inches square and equation 3 is for area in centimeters square. The area, in square inches or square centimeters is the top copper area including the gate and source pads.

$$R_{\Theta JA} = 26.51 + \frac{19.84}{(0.262 + Area)}$$
 (EQ. 2)

Area in Inches Squared

$$R_{\theta JA} = 26.51 + \frac{128}{(1.69 + Area)}$$
 (EQ. 3)

Area in Centimeters Squared

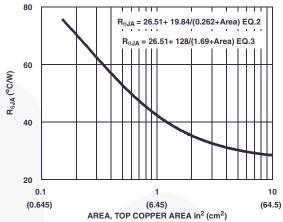
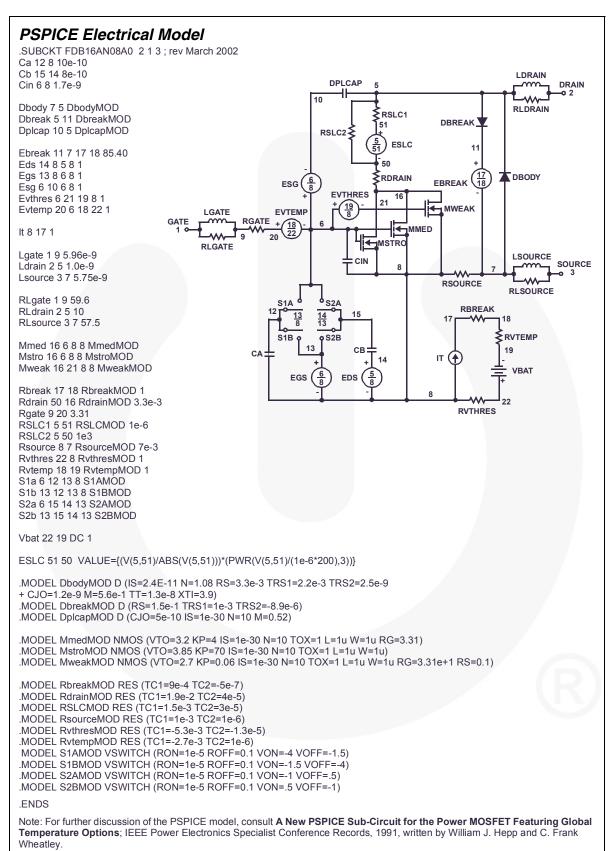
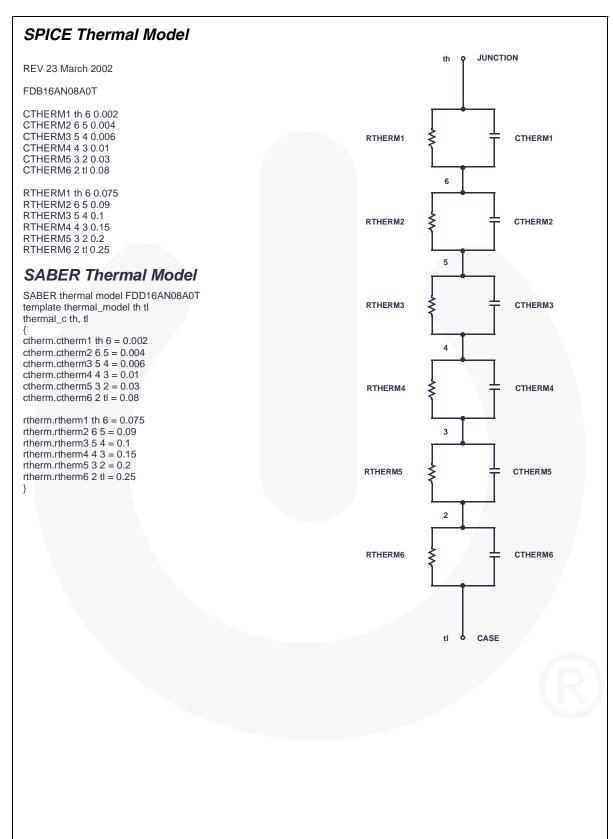


Figure 21. Thermal Resistance vs Mounting Pad Area



SABER Electrical Model rev March 2002 template FDB16AN08A0 n2,n1,n3 electrical n2,n1,n3 var i iscl dp..model dbodymod = (isl=2.4e-11,nl=1.08,rs=3.3e-3,trs1=2.2e-3,trs2=2.5e-9,cjo=1.2e-9,m=5.6e-1,tt=1.3e-8,xti=3.9) dp..model dbreakmod = (rs=1.5e-1,trs1=1e-3,trs2=-8.9e-6) dp..model dplcapmod = (cjo=5e-10,isl=10e-30,nl=10,m=0.52) m..model mmedmod = (type=_n,vto=3.2,kp=4,is=1e-30, tox=1) m..model mstrongmod = (type=_n,vto=3.85,kp=70,is=1e-30, tox=1) m..model mweakmod = (type=_n,vto=2.7,kp=0.06,is=1e-30, tox=1,rs=0.1) IDRAIN sw_vcsp..model s1amod = (ron=1e-5,roff=0.1,von=-4,voff=-1.5) DPLCAP DRAIN sw_vcsp..model s1bmod = (ron=1e-5,roff=0.1,von=-1.5,voff=-4) 10 sw_vcsp..model s2amod = (ron=1e-5,roff=0.1,von=-1,voff=.5) RLDRAIN sw_vcsp..model s2bmod = (ron=1e-5,roff=0.1,von=.5,voff=-1) ₹RSLC1 c.ca n12 n8 = 10e-1051 RSLC2 ₹ c.cb n15 n14 = 8e-10 ISCL c.cin n6 n8 = 1.7e-9DBREAK 50 dp.dbody n7 n5 = model=dbodymod RDRAIN dp.dbreak n5 n11 = model=dbreakmod <u>6</u> 8 **ESG** dp.dplcap n10 n5 = model=dplcapmod DRODY **EVTHRES** 21 MWFAK spe.ebreak n11 n7 n17 n18 = 85.40 _{GATE} LGATE EVTEMP **RGATE** MMED spe.eds n14 n8 n5 n8 = 1 **EBREA** Ιg 20 spe.egs n13 n8 n6 n8 = 1 MSTRO RLGATE spe.esg n6 n10 n6 n8 = 1 **LSOURCE** spe.evthres n6 n21 n19 n8 = 1 CIN SOURCE spe.evtemp n20 n6 n18 n22 = 1 **RSOURCE** RLSOURCE i.it n8 n17 = 1RBREAK I.lgate n1 n9 = 5.96e-917 I.ldrain n2 n5 = 1.0e-9RVTEMP I.lsource n3 n7 = 5.75e-9CB 19 CA IT 14 res.rlgate n1 n9 = 59.6 **VBAT** res.rldrain n2 n5 = 10 **EGS** res.rlsource n3 n7 = 57.5 m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u **RVTHRES** m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u res.rbreak n17 n18 = 1, tc1=9e-4,tc2=-5e-7 res.rdrain n50 n16 = 3.3e-3, tc1=1.9e-2,tc2=4e-5 res.rgate n9 n20 = 3.31 res.rslc1 n5 n51 = 1e-6, tc1=1.5e-3,tc2=3e-5 res.rslc2 n5 n50 = 1e3res.rsource n8 n7 = 7e-3, tc1=1e-3,tc2=1e-6 res.rvthres n22 n8 = 1, tc1=-5.3e-3,tc2=-1.3e-5 res.rvtemp n18 n19 = 1, tc1=-2.7e-3,tc2=1e-6 sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod v.vbat n22 n19 = dc=1 equations { i (n51->n50) +=iscl iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6/200))**3))



Mechanical Dimensions

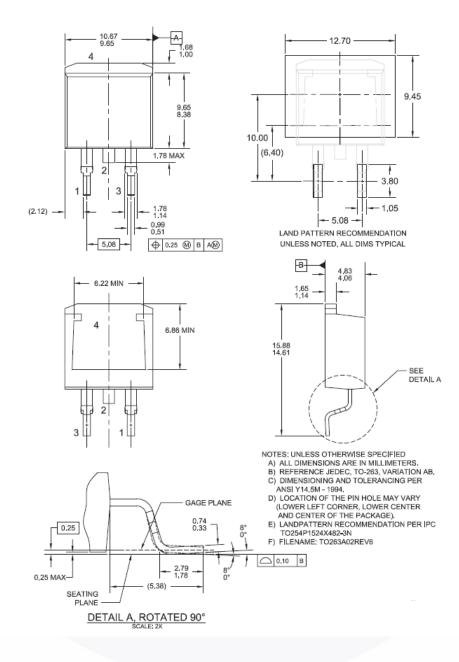


Figure 22. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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